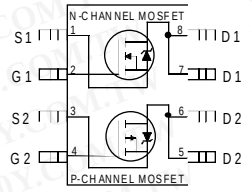
International
IOR Rectifier

PD - 9.1242B

IRF7307

HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- Dual N and P Channel Mosfet
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching



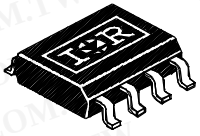
Top View

	N-Ch	P-Ch
V_{DSS}	20V	-20V
$R_{DS(on)}$	0.050Ω	0.090Ω

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.


SO-8

Absolute Maximum Ratings

	Parameter	Max.		Units
		N-Channel	P-Channel	
I_D @ T_A = 25°C	10 Sec. Pulse Drain Current, V_{GS} @ 4.5V	5.7	-4.7	A
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 4.5V	5.2	-4.3	
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 4.5V	4.1	-3.4	
I_{DM}	Pulsed Drain Current ①	21	-17	
P_D @T_A = 25°C	Power Dissipation	2.0		W
	Linear Derating Factor	0.016		W/°C
V_{GS}	Gate-to-Source Voltage	± 12		V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	-5.0	V/ns
T_J,T_{STG}	Junction and Storage Temperature Range	-55 to + 150		°C

Thermal Resistance Ratings

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient④	——	62.5	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter		Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	N-Ch	20	—	—	V	V_{GS} = 0V, I_D = 250µA
		P-Ch	-20	—	—		V_{GS} = 0V, I_D = -250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	N-Ch	—	0.044	—	V/°C	Reference to 25°C, I_D = 1mA
		P-Ch	—	-0.012	—		Reference to 25°C, I_D = -1mA
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	N-Ch	—	—	0.050	Ω	V_{GS} = 4.5V, I_D = 2.6A ③
			—	—	0.070		V_{GS} = 2.7V, I_D = 2.2A ③
		P-Ch	—	—	0.090		V_{GS} = -4.5V, I_D = -2.2A ③
			—	—	0.140		V_{GS} = -2.7V, I_D = -1.8A ③
$V_{GS(th)}$	Gate Threshold Voltage	N-Ch	0.70	—	—	V	V_{DS} = V_{GS}, I_D = 250µA
		P-Ch	-0.70	—	—		V_{DS} = V_{GS}, I_D = -250µA
g_{fs}	Forward Transconductance	N-Ch	8.30	—	—	S	V_{DS} = 15V, I_D = 2.6A ③
		P-Ch	4.00	—	—		V_{DS} = -15V, I_D = -2.2A ③
I_{DSS}	Drain-to-Source Leakage Current	N-Ch	—	—	1.0	µA	V_{DS} = 16V, V_{GS} = 0V
		P-Ch	—	—	-1.0		V_{DS} = -16V, V_{GS} = 0V,
		N-Ch	—	—	25		V_{DS} = 16V, V_{GS} = 0V, T_J = 125°C
		P-Ch	—	—	-25		V_{DS} = -16V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	N-P	—	—	±100		V_{GS} = ± 12V
Q_g	Total Gate Charge	N-Ch	—	—	20	nC	N-Channel I_D = 2.6A, V_{DS} = 16V, V_{GS} = 4.5V ③ P-Channel I_D = -2.2A, V_{DS} = -16V, V_{GS} = -4.5V
		P-Ch	—	—	22		
Q_{gs}	Gate-to-Source Charge	N-Ch	—	—	2.2		
		P-Ch	—	—	3.3		
Q_{gd}	Gate-to-Drain ("Miller") Charge	N-Ch	—	—	8.0		
		P-Ch	—	—	9.0		
$t_{d(on)}$	Turn-On Delay Time	N-Ch	—	9.0	—	ns	N-Channel V_{DD} = 10V, I_D = 2.6A, R_G = 6.0Ω, R_D = 3.8Ω ③ P-Channel V_{DD} = -10V, I_D = -2.2A, R_G = 6.0Ω, R_D = 4.5Ω
		P-Ch	—	8.4	—		
t_r	Rise Time	N-Ch	—	42	—		
		P-Ch	—	26	—		
$t_{d(off)}$	Turn-Off Delay Time	N-Ch	—	32	—		
		P-Ch	—	51	—		
t_f	Fall Time	N-Ch	—	51	—		
		P-Ch	—	33	—		
L_D	Internal Drain Inductace	N-P	—	4.0	—	nH	Between lead tip and center of die contact
L_S	Internal Source Inductance	N-P	—	6.0	—		
C_{iss}	Input Capacitance	N-Ch	—	660	—	pF	N-Channel V_{GS} = 0V, V_{DS} = 15V, f = 1.0MHz ③ P-Channel V_{GS} = 0V, V_{DS} = -15V, f = 1.0MHz
		P-Ch	—	610	—		
C_{oss}	Output Capacitance	N-Ch	—	280	—		
		P-Ch	—	310	—		
C_{rss}	Reverse Transfer Capacitance	N-Ch	—	140	—		
		P-Ch	—	170	—		

Source-Drain Ratings and Characteristics

	Parameter		Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	N-Ch	—	—	2.5	A	
		P-Ch	—	—	-2.5		
I_{SM}	Pulsed Source Current (Body Diode) ①	N-Ch	—	—	21		
		P-Ch	—	—	-17		
V_{SD}	Diode Forward Voltage	N-Ch	—	—	1.0	V	T_J = 25°C, I_S = 1.8A, V_{GS} = 0V ③
		P-Ch	—	—	-1.0		T_J = 25°C, I_S = -1.8A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	N-Ch	—	29	44	ns	N-Channel T_J = 25°C, I_F = 2.6A, di/dt = 100A/µs P-Channel T_J = 25°C, I_F = -2.2A, di/dt = 100A/µs ③
		P-Ch	—	56	84		
Q_{rr}	Reverse Recovery Charge	N-Ch	—	22	33	nC	
		P-Ch	—	71	110		
t_{on}	Forward Turn-On Time	N-P	Intrinsic turn-on time is neglegible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 23)

② N-Channel I_{SD} ≤ 2.6A, di/dt ≤ 100A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C
P-Channel I_{SD} ≤ -2.2A, di/dt ≤ 50A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C

③ Pulse width ≤ 300µs; duty cycle ≤ 2%.

④ Surface mounted on FR-4 board, t ≤ 10sec.

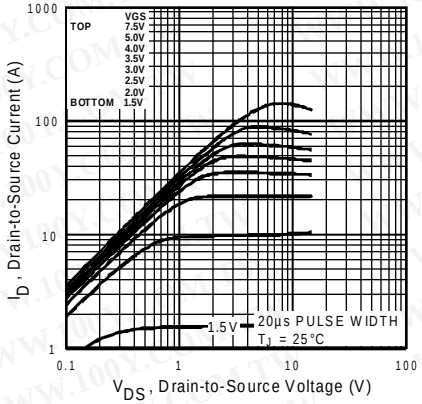


Fig 1. Typical Output Characteristics

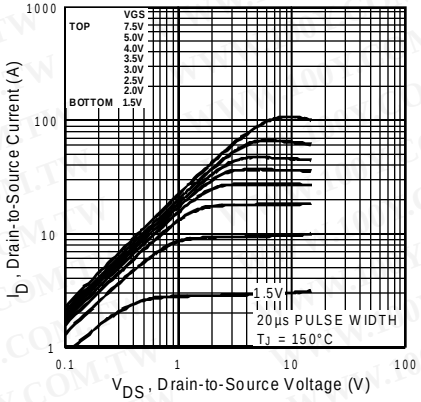


Fig 2. Typical Output Characteristics

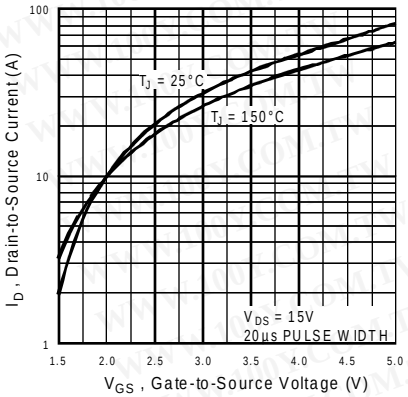


Fig 3. Typical Transfer Characteristics

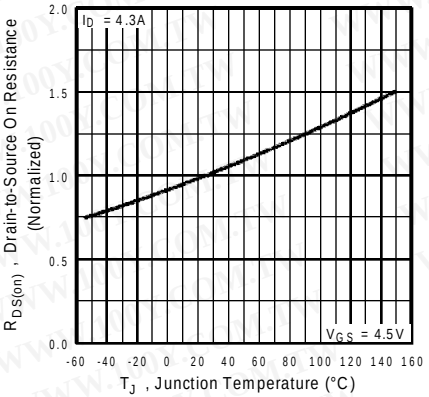


Fig 4. Normalized On-Resistance Vs. Temperature

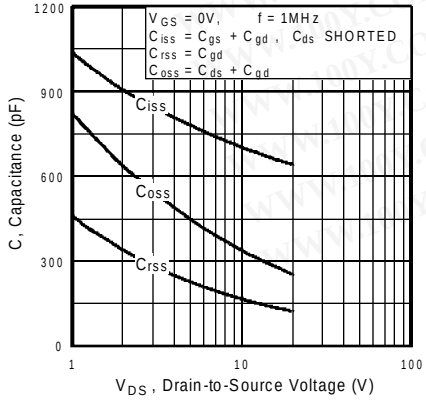


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

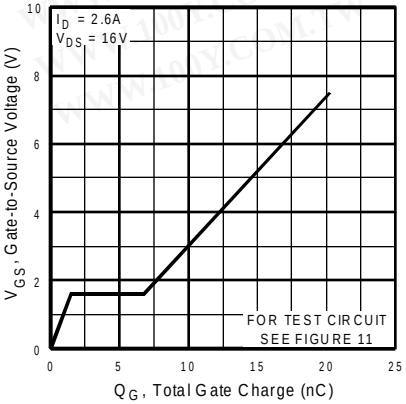


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

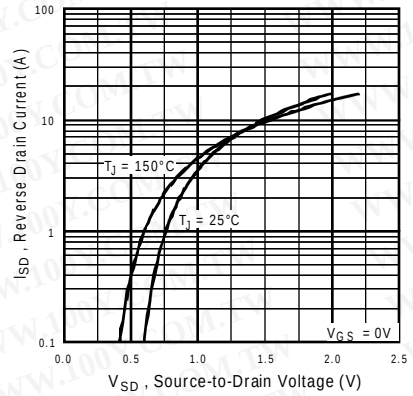


Fig 7. Typical Source-Drain Diode Forward Voltage

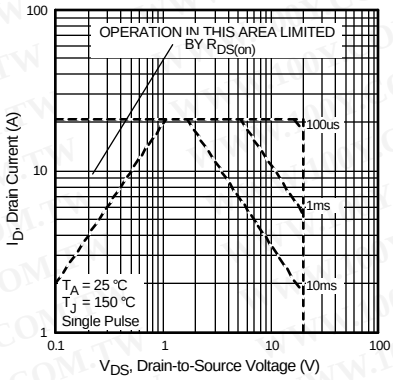


Fig 8. Maximum Safe Operating Area

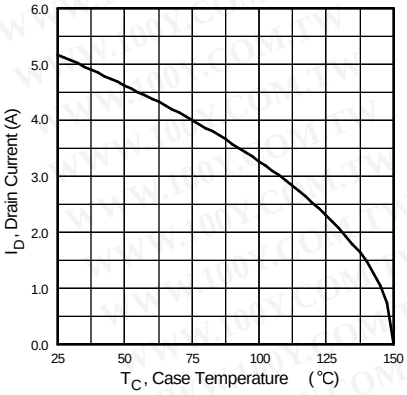


Fig 9. Maximum Drain Current Vs. Ambient Temperature

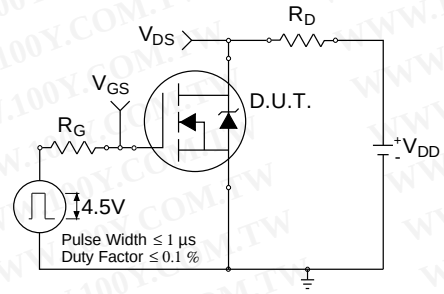


Fig 10a. Switching Time Test Circuit

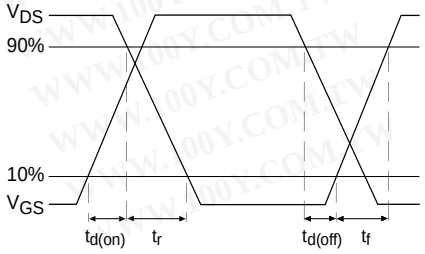


Fig 10b. Switching Time Waveforms

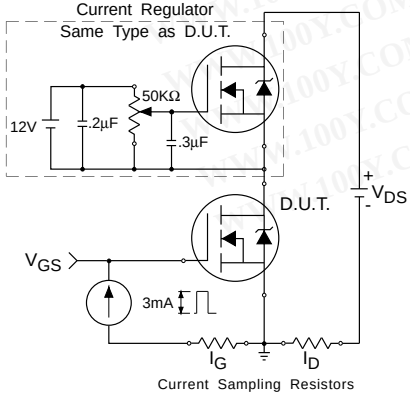


Fig 11a. Gate Charge Test Circuit

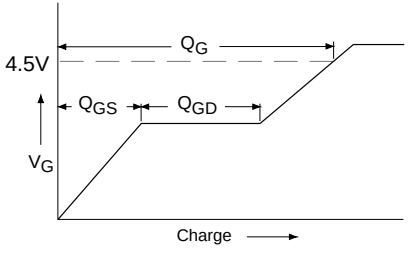


Fig 11b. Basic Gate Charge Waveform

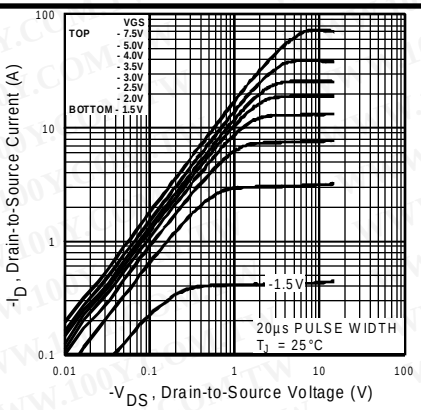


Fig 12. Typical Output Characteristics

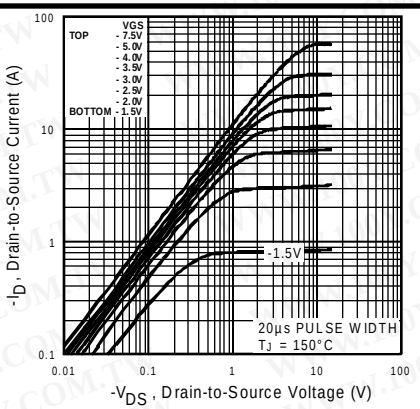


Fig 13. Typical Output Characteristics

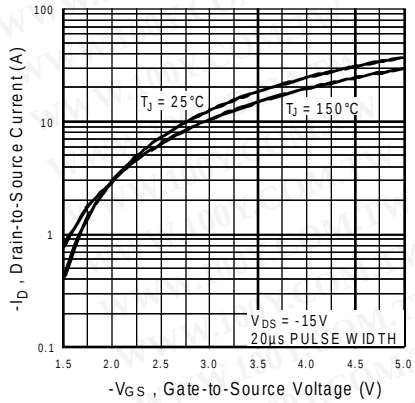


Fig 14. Typical Transfer Characteristics

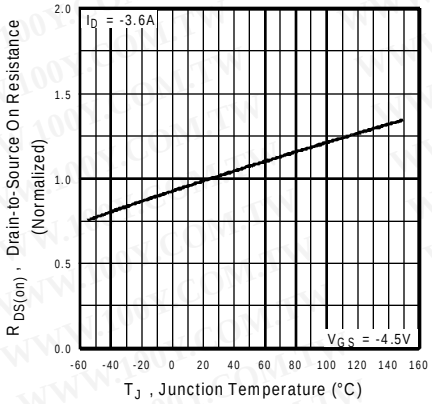


Fig 15. Normalized On-Resistance Vs. Temperature

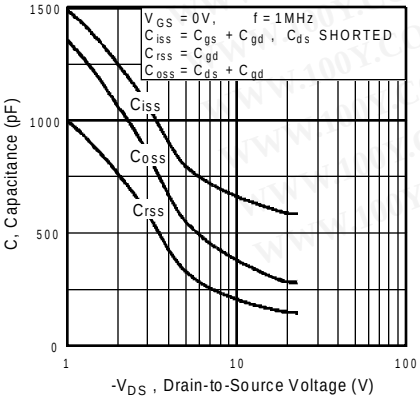


Fig 16. Typical Capacitance Vs. Drain-to-Source Voltage

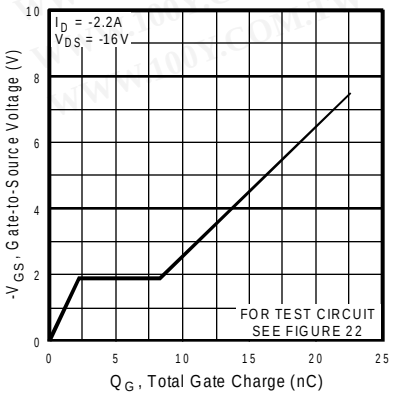


Fig 17. Typical Gate Charge Vs. Gate-to-Source Voltage

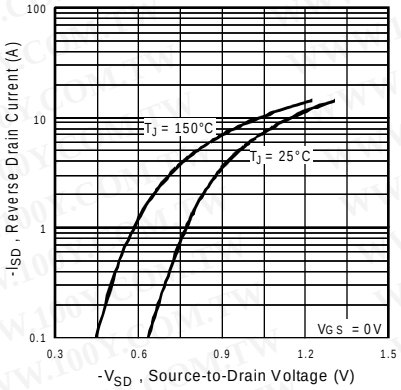


Fig 18. Typical Source-Drain Diode Forward Voltage

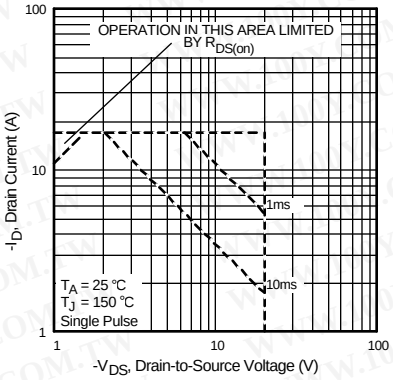


Fig 19. Maximum Safe Operating Area

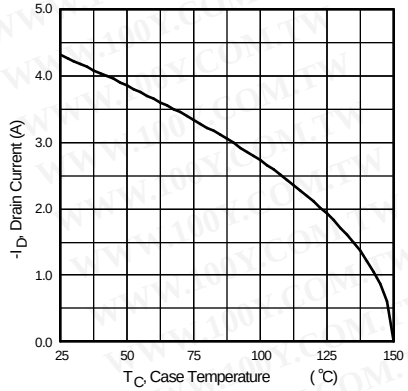


Fig 20. Maximum Drain Current Vs. Ambient Temperature

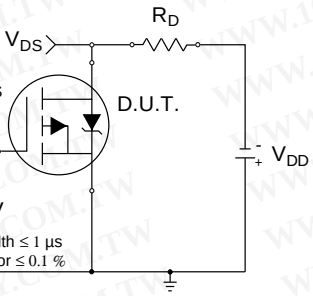


Fig 21a. Switching Time Test Circuit

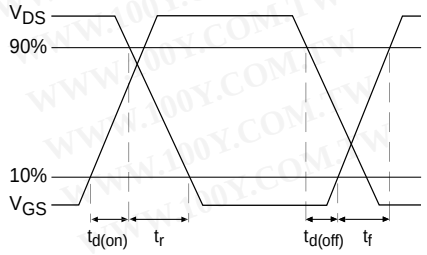


Fig 21b. Switching Time Waveforms

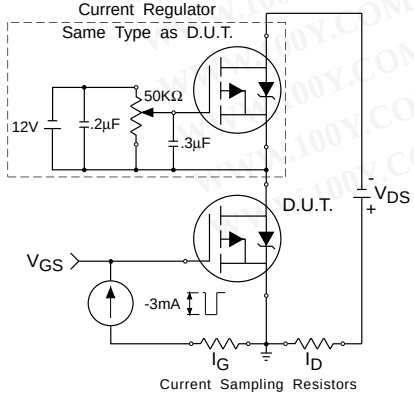


Fig 22a. Gate Charge Test Circuit

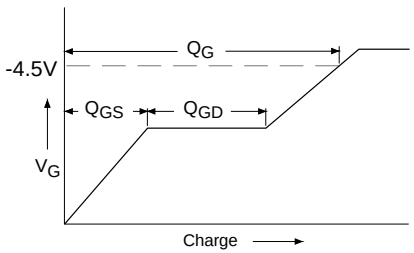


Fig 22b. Basic Gate Charge Waveform

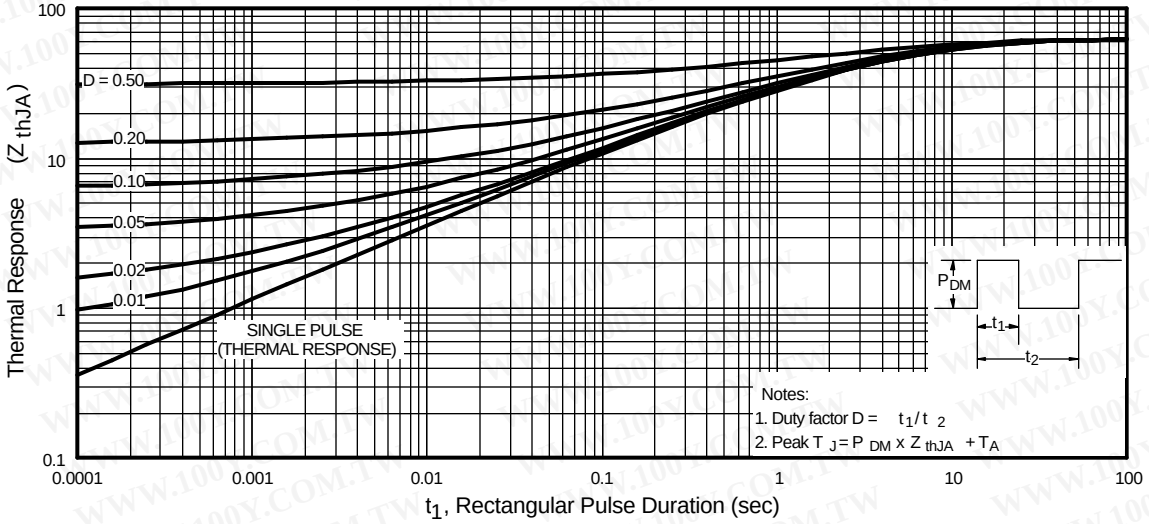
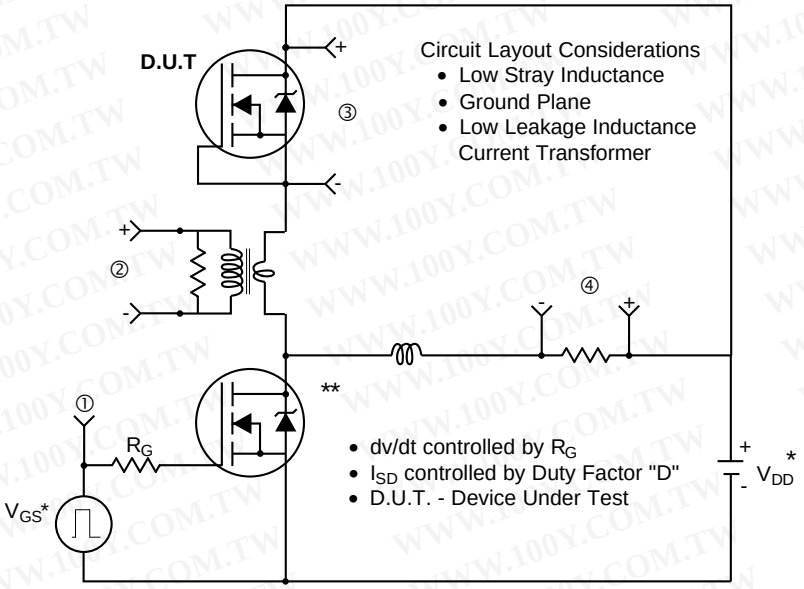
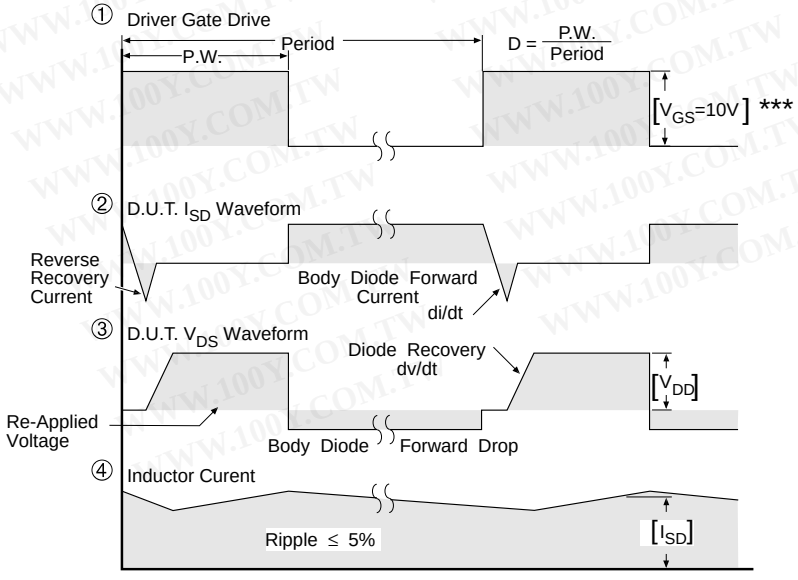


Fig 23. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel
** Use P-Channel Driver for P-Channel Measurements



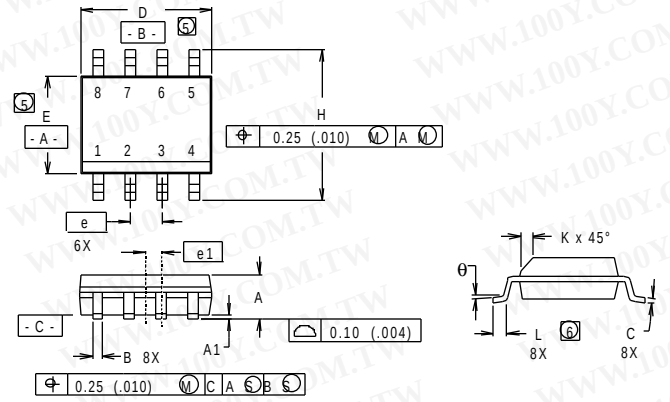
*** V_{GS} = 5.0V for Logic Level and 3V Drive Devices

Fig 24. For N and P Channel HEXFETS

Package Outline

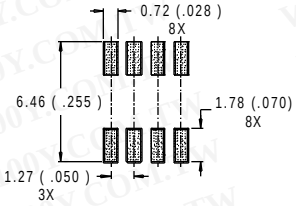
SO-8 Outline

Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
θ	0°	8°	0°	8°

RECOMMENDED FOOTPRINT



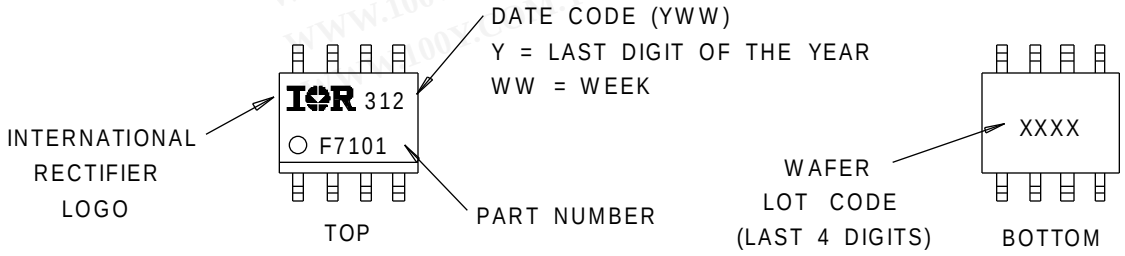
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS
   MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
6. DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

Part Marking Information

SO-8

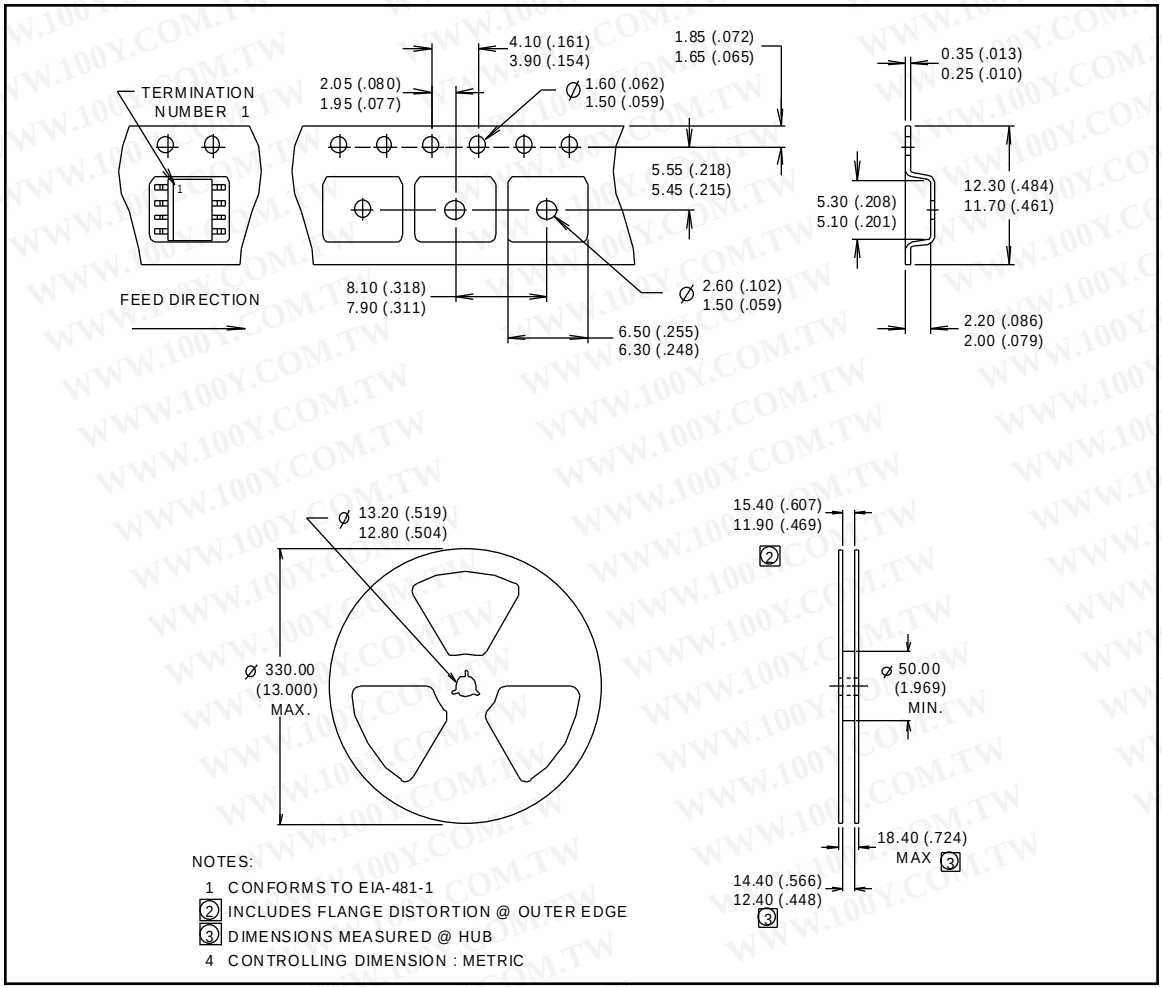
EXAMPLE : THIS IS AN IRF7101



Tape & Reel Information

SO-8

Dimensions are shown in millimeters (inches)



NOTES:

1 CONFORMS TO EIA-481-1

2 INCLUDES FLANGE DISTORTION @ OUTER EDGE

3 DIMENSIONS MEASURED @ HUB

4 CONTROLLING DIMENSION : METRIC

International
IOR Rectifier

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331
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